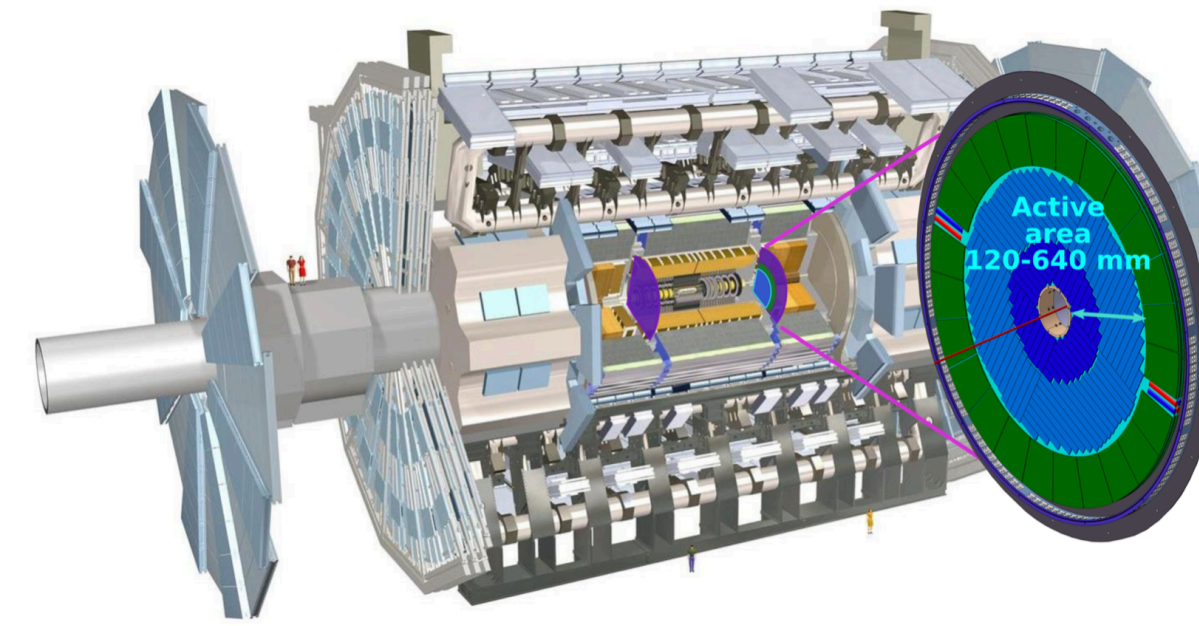


24th-28th October

**VERTEX** 2022

Tateyama Resort Hotel, Japan



# Performance studies of the Low Gain Avalanche Detectors for the ATLAS High Granularity Timing Detector in beam tests

**Valentina Raskina**  
on behalf of the ATLAS HGTD Group

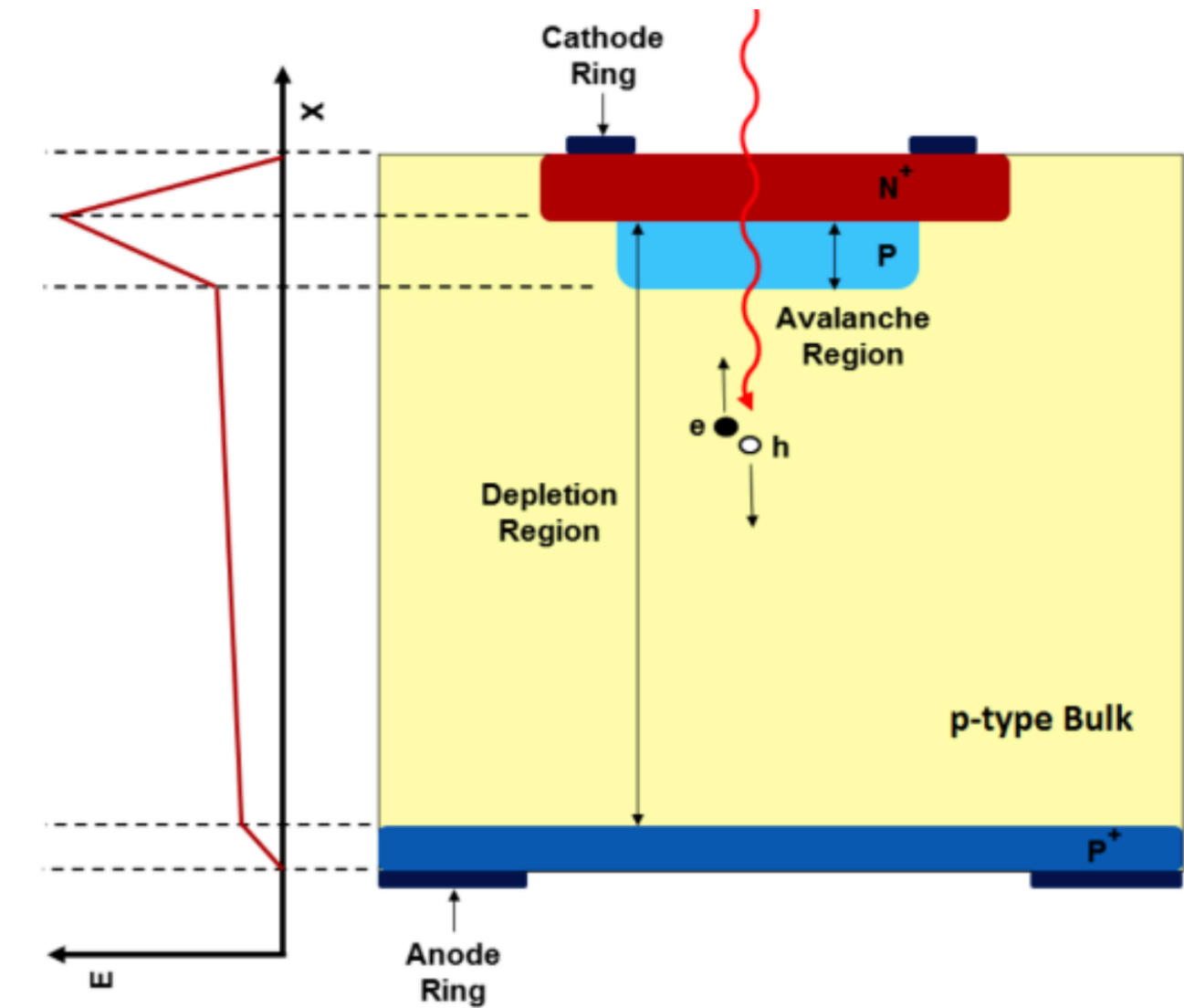
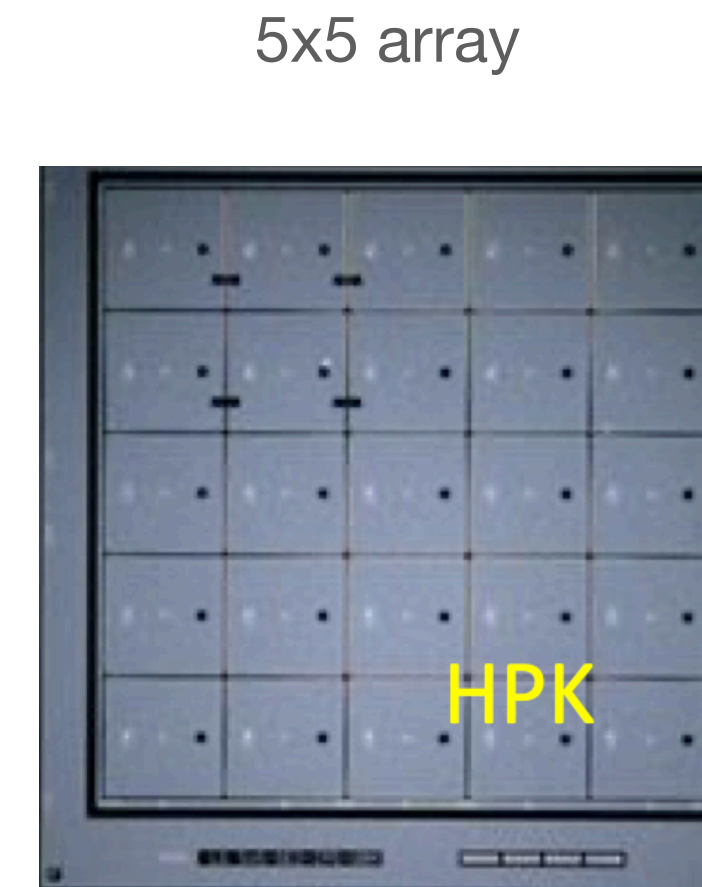


- Low Gain Avalanche Detectors (LGAD)
- Single Event Burnout
- Sensors list
- Test Beam setups: DESY, CERN SPS
- Results
- Conclusion



# Low Gain Avalanche Detector (LGAD)

- n on p sensor with a p-type multiplication layer of thickness  $\sim 50\mu\text{m}$
- Moderate internal gain (8-50)
- The higher the Bias Voltage applied, the higher the gain
- Fast rise time (0.5-0.8 ns)
- Time resolution before irradiation  $\sim 30\text{ps}$
- 15 x 15 pads of size  $1.3 \times 1.3\text{mm}^2$

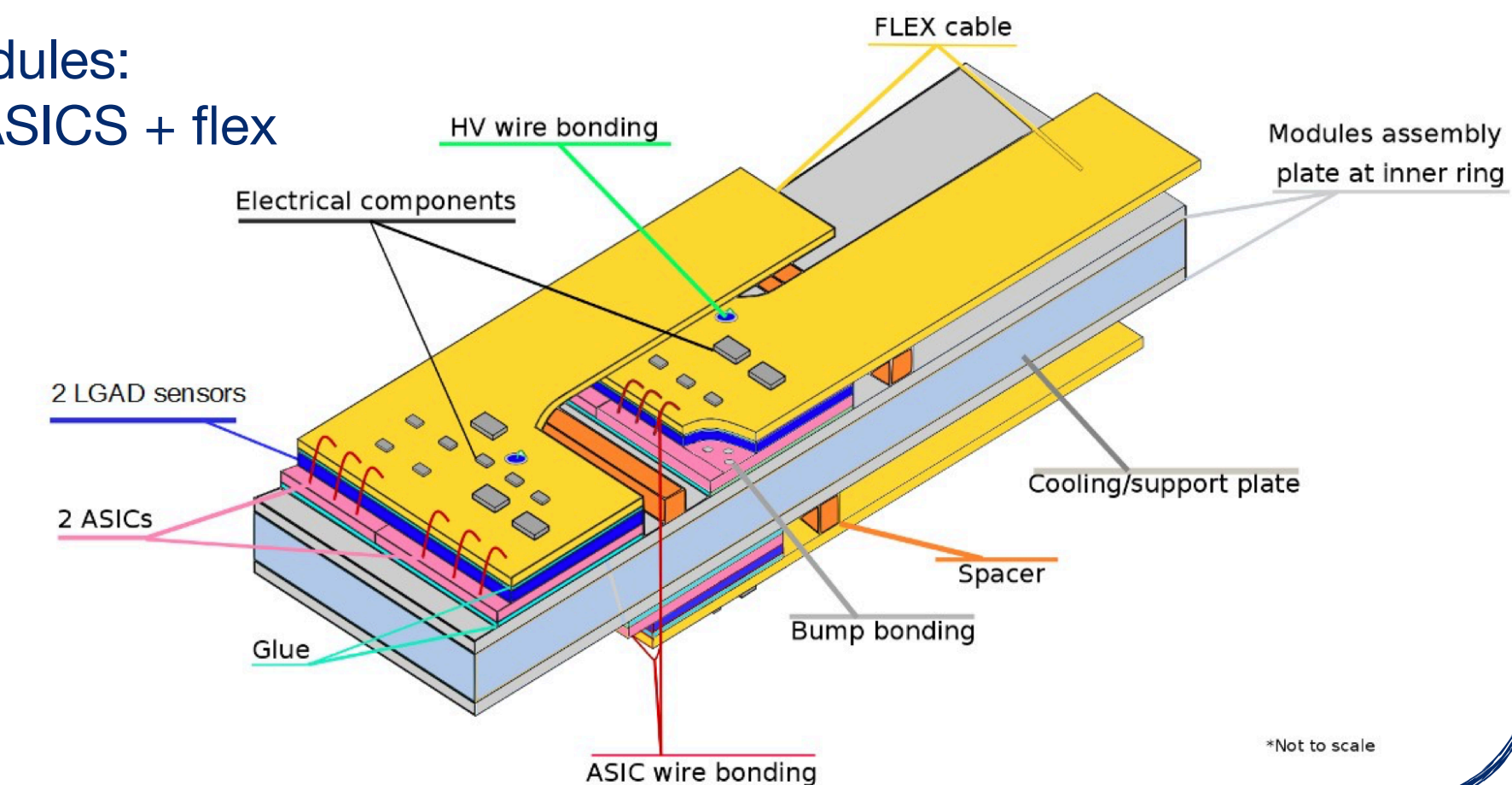


## Key design requirements:

- ❖ Radiation hardness
  - ❖ Minimum required charge collection of 4fC
  - ❖  $< 70\text{ps}$  time resolution
  - ❖  $> 95\%$  efficiency
- } at maximum irradiation of  $2.5 \times 10^{15} \text{ n}_{eq}/\text{cm}^2$

## Read out : ASICS integrated circuits ALTIROC

8032 modules:  
2 sensors + 2 ASICS + flex

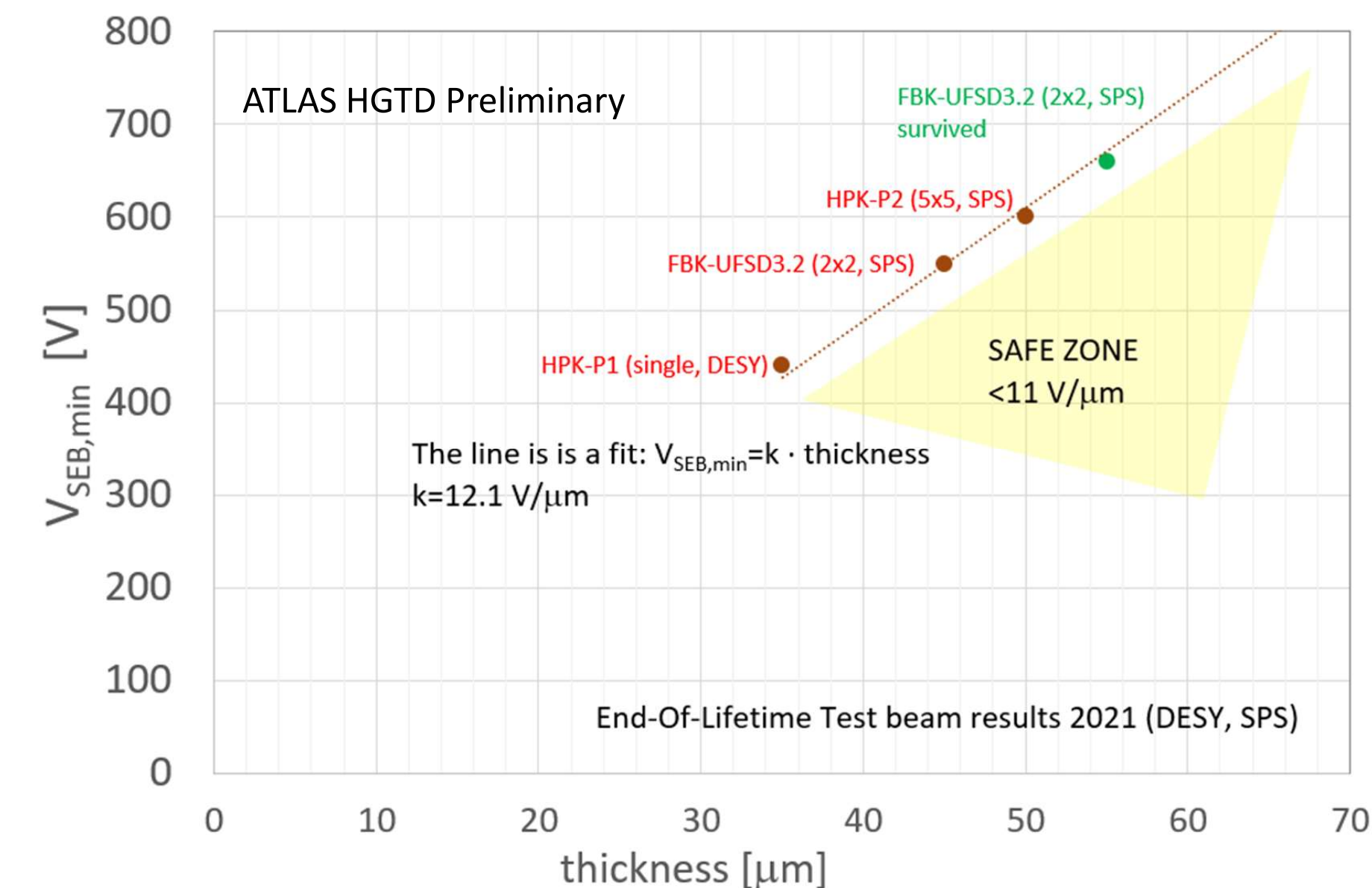
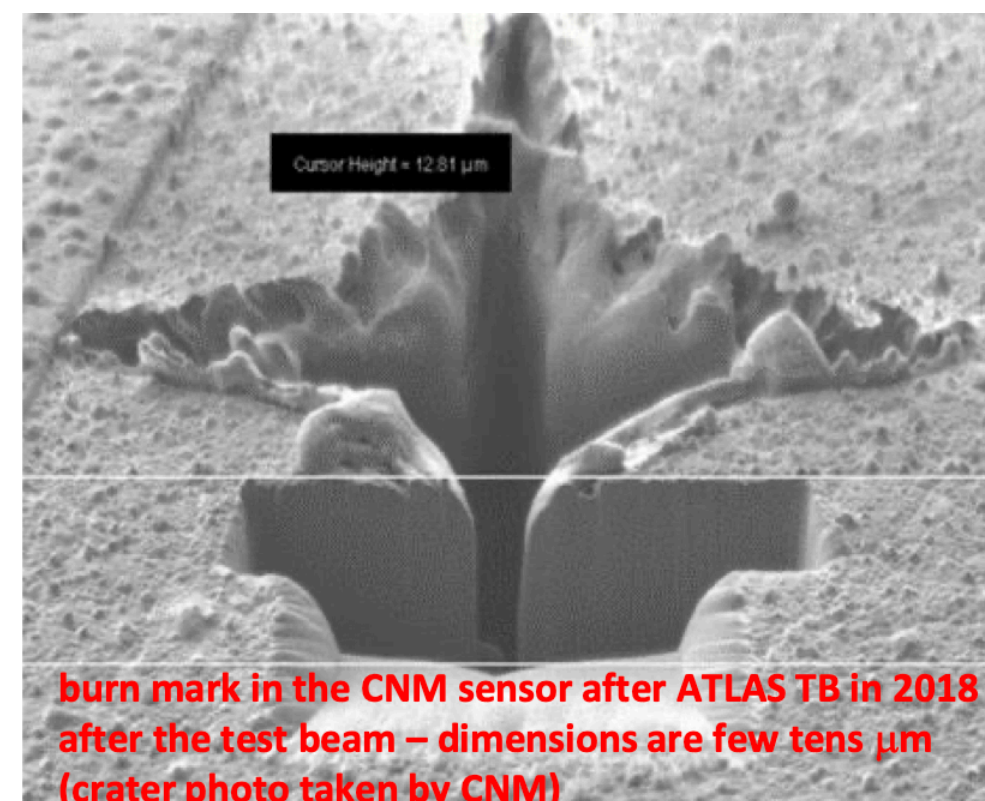




# Single Event Burnout

The process of large current in narrow path is called “Single Event Burnout”

- The field collapse in the presence of high concentration of free carriers is the probable cause
- Need to be ensured that sensors can meet project requirements without risk of SEB
- **Electric field** ( $V_{\text{bias}}/\text{thickness}$ ) is the key parameter determining the fatality

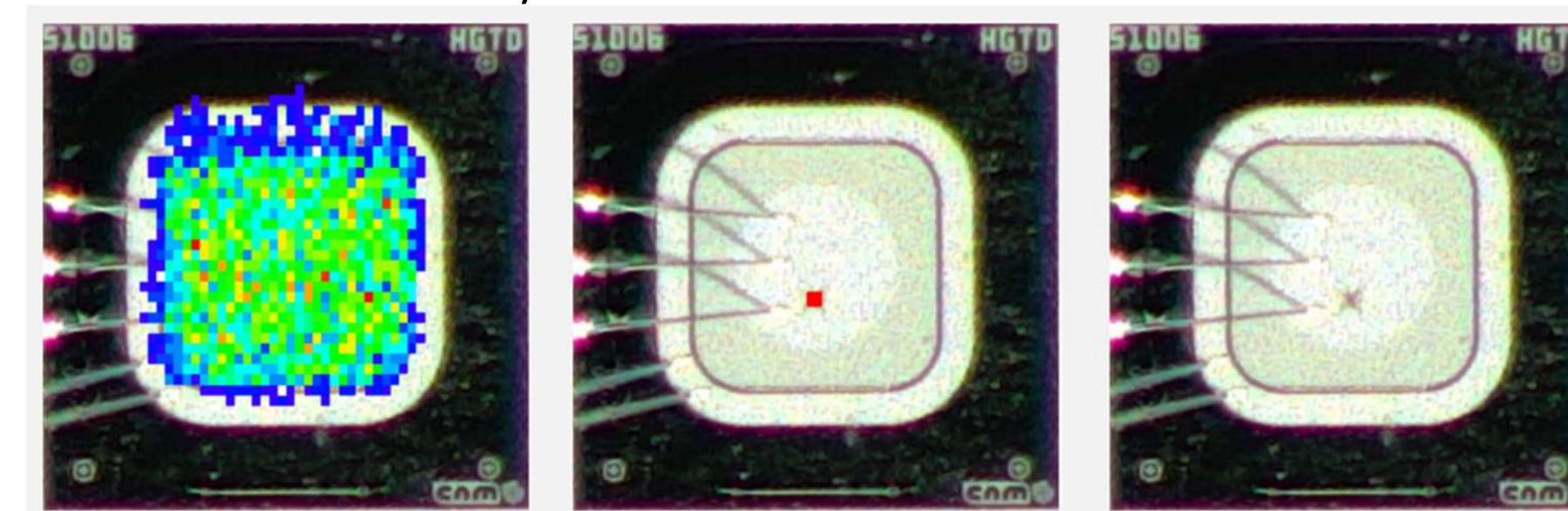


In 2019-2021 Test beam campaigns, the sensors mortality was observed

**Mortality test beams** were organised at DESY in June 2021 (3 GeV electrons) and CERN SPS in November 2021 (120 GeV pions)

- 74 sensors tested, 55 survived to voltages expected to meet HGTD specs
- Defined safe zone < 11V/μm

ATLAS HGTD Preliminary



Typical Single Event Burnout mark is shown in the right plot (2019 DESY test-beam with 5 GeV e). The reconstructed track in the SEB event pointed to the location of the burn mark (middle and right plot). All the reconstructed tracks distribution across the detector before SEB is shown in the left plot.



# Sensors presented in this talk

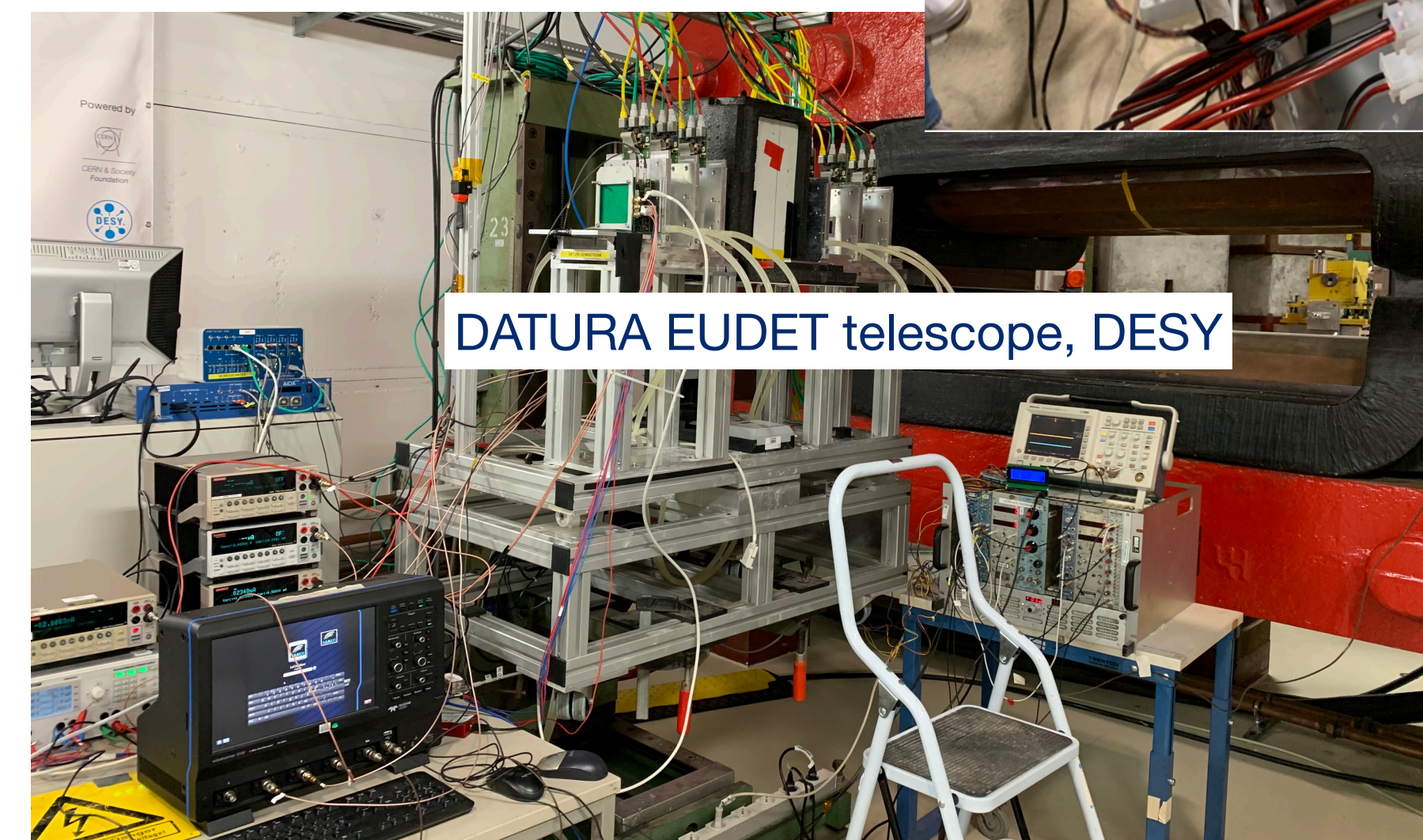
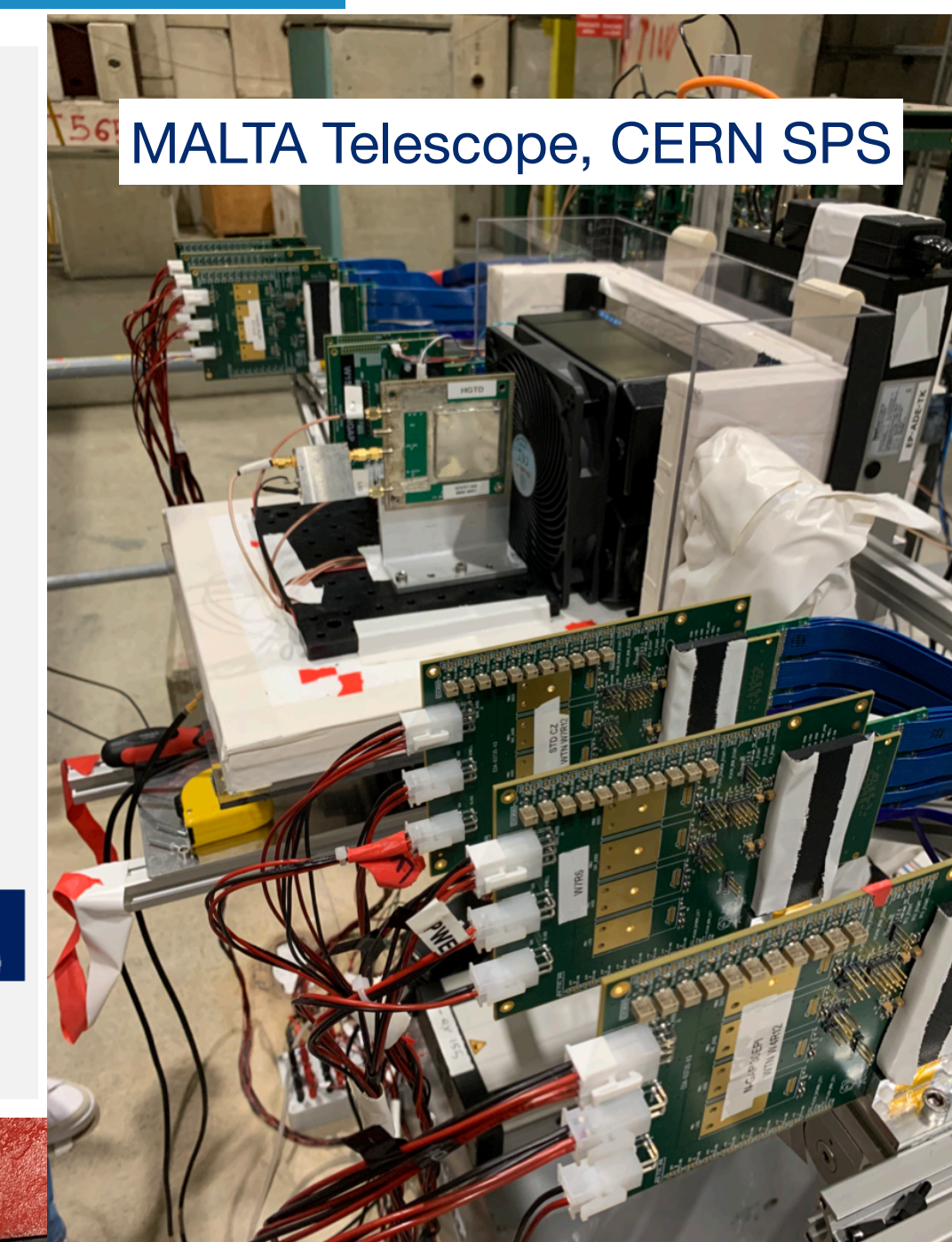
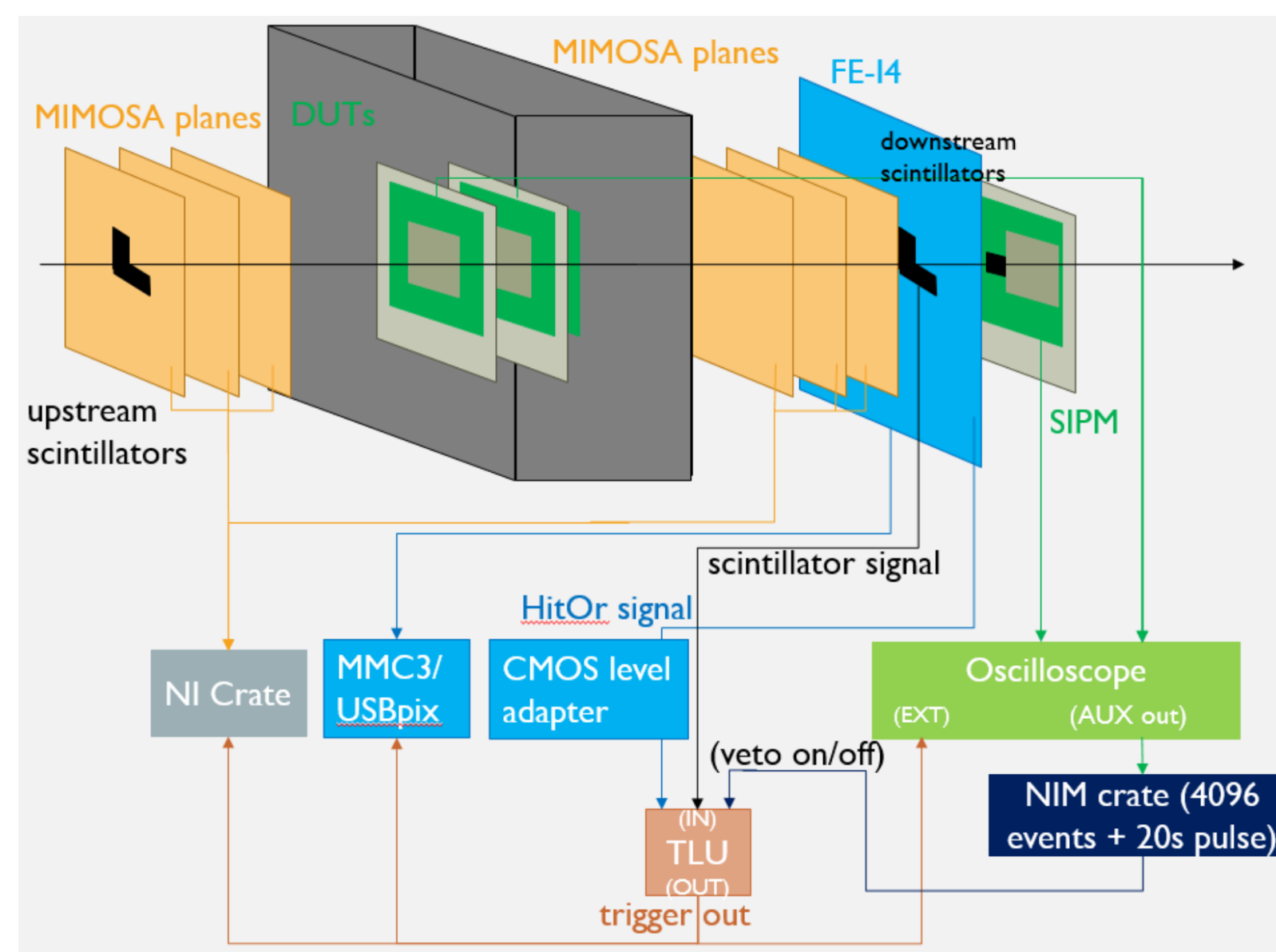
Device name	Manufacturer	Implant	Fluence [ $n_{eq}/cm^2$ ]	Test Beam	Temperatures [°C]
FBK-UFSD3.2 W19	FBK	Boron + C diffused	$1.5 \times 10^{15}$ $2.5 \times 10^{15}$	DESY DESY/CERN	-40 to -30 -46 to -26 / -20
USTC-IMEv2.1 W17	USTC-IME	Boron + C diffused	$1.5 \times 10^{15}$ $2.5 \times 10^{15}$	DESY DESY	-39 to -24 -43 to -29
IHEP-IMEv2 W7Q2	IHEP-IME	Boron + C diffused	$1.5 \times 10^{15}$ $2.5 \times 10^{15}$	DESY CERN	-43 to -30 -20

All sensors irradiated with reactor neutrons at JSI and annealed for 80 mins @ 60°C



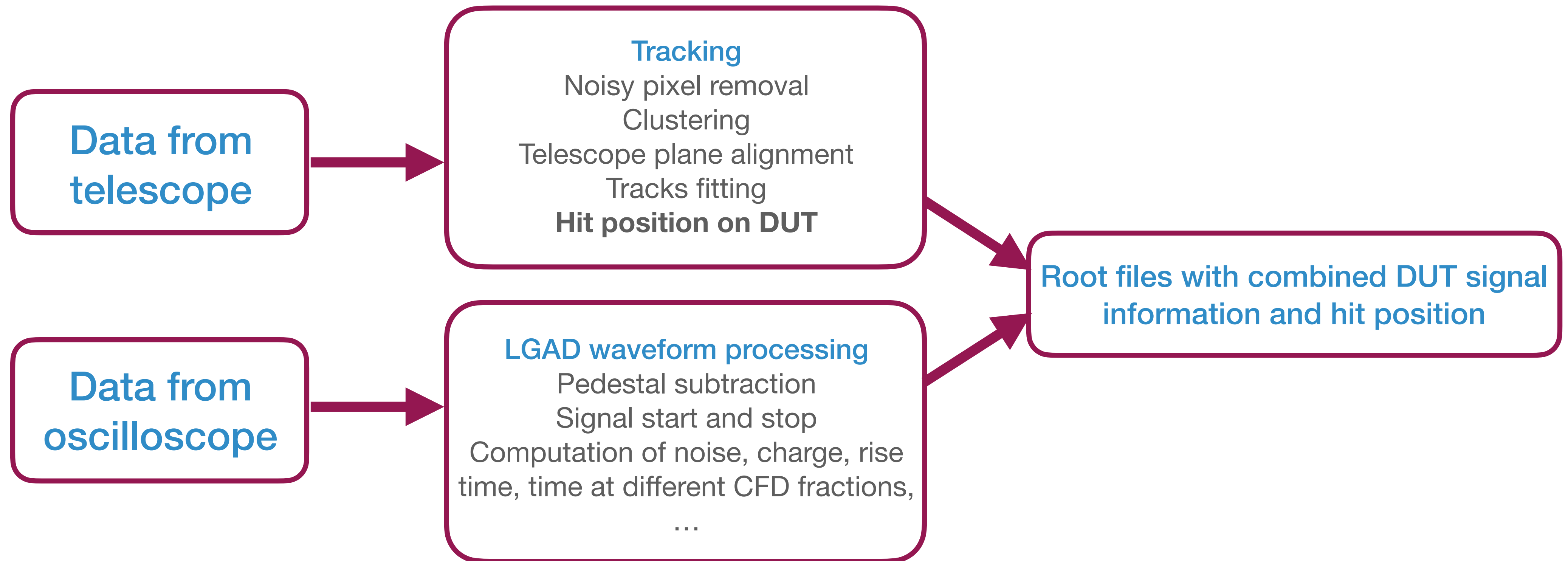
# Test Beam setup

- **Sensors:**  
 DESY: 12 sensors tested (5 GeV electrons)  
 CERN: 10 sensors tested (120 GeV pions)  
 Oscilloscope for **waveform readout**
- **Tracking with 6 telescope planes:**  
 DESY: DATURA EUDET telescope with **MIMOSA** chips + FEi4 (trigger/ROI)  
 CERN: MALTA telescope with **MALTA** chips
- **Time reference:**  
 DESY: **SiPM** (resolution of ~66ps)  
 CERN: **Unirradiated LGAD** (resolution of ~35ps)
- **Cooling:**  
 DESY: Cold box with dry ice, 2 PT100 sensors for temperature monitoring  
 CERN: Cold box with climate chamber keeps temperature at -20 C°
- **2 Devices Under Tests (DUT)** simultaneously
- Sensors were studied at the safe from SEB voltages





# Data processing workflow

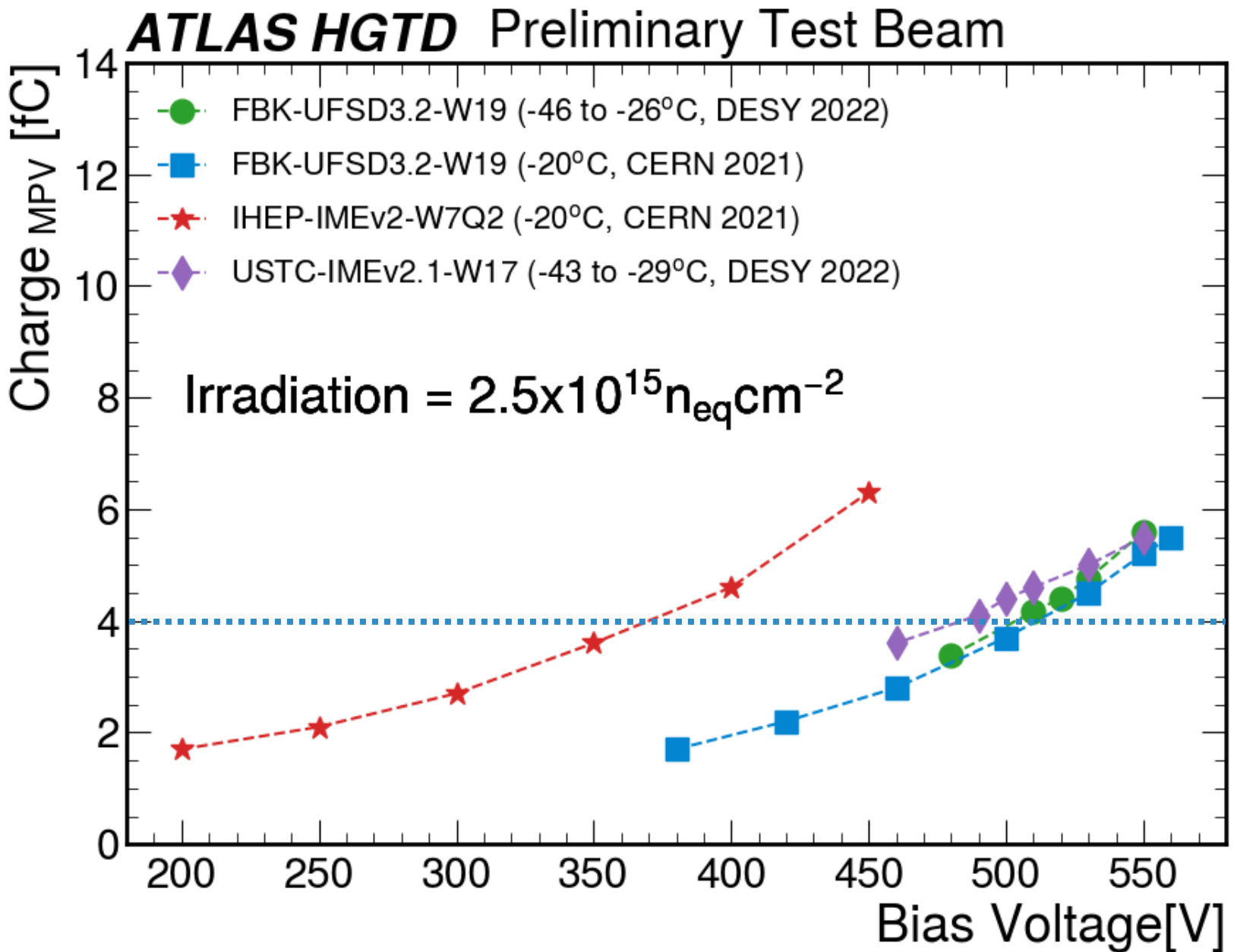
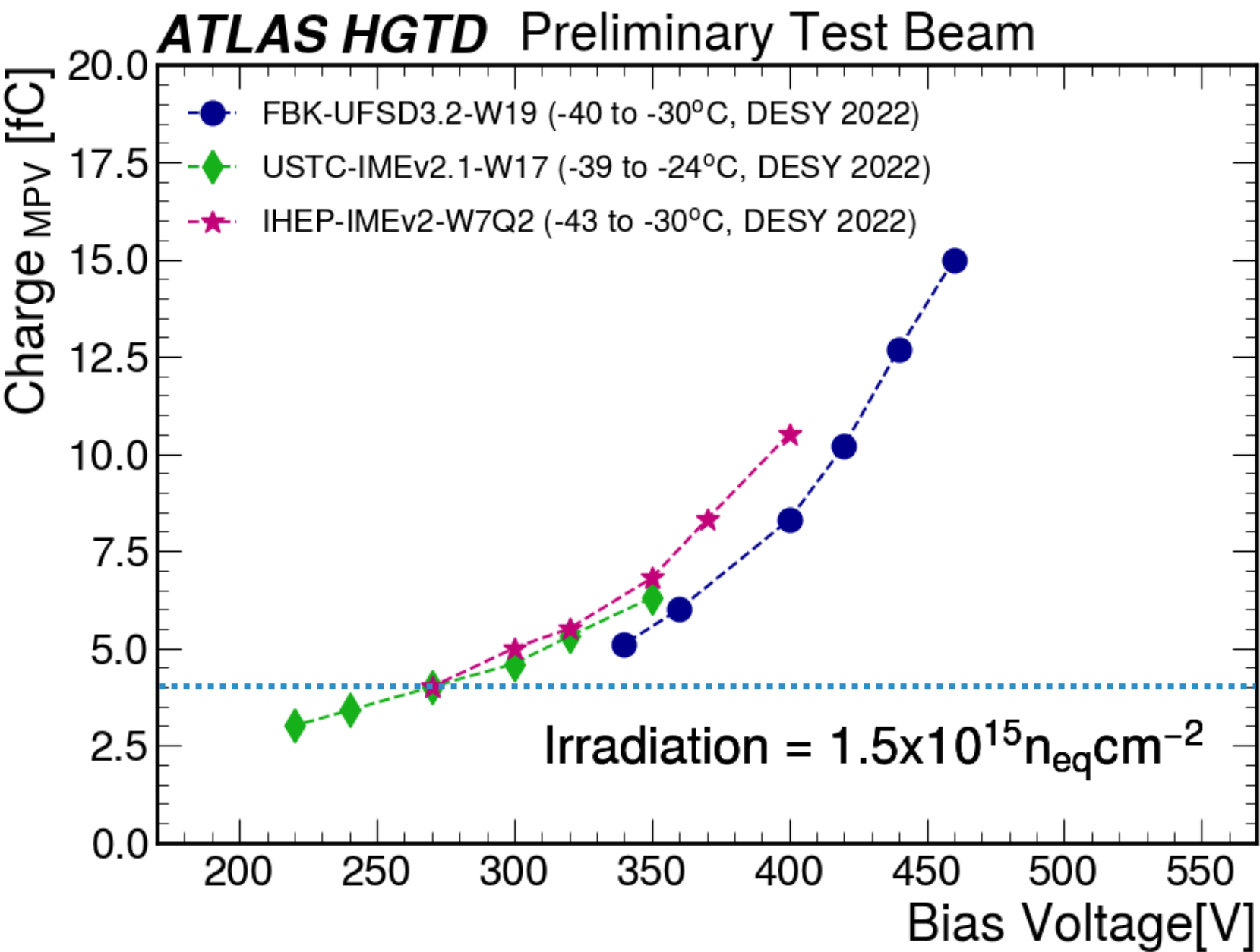
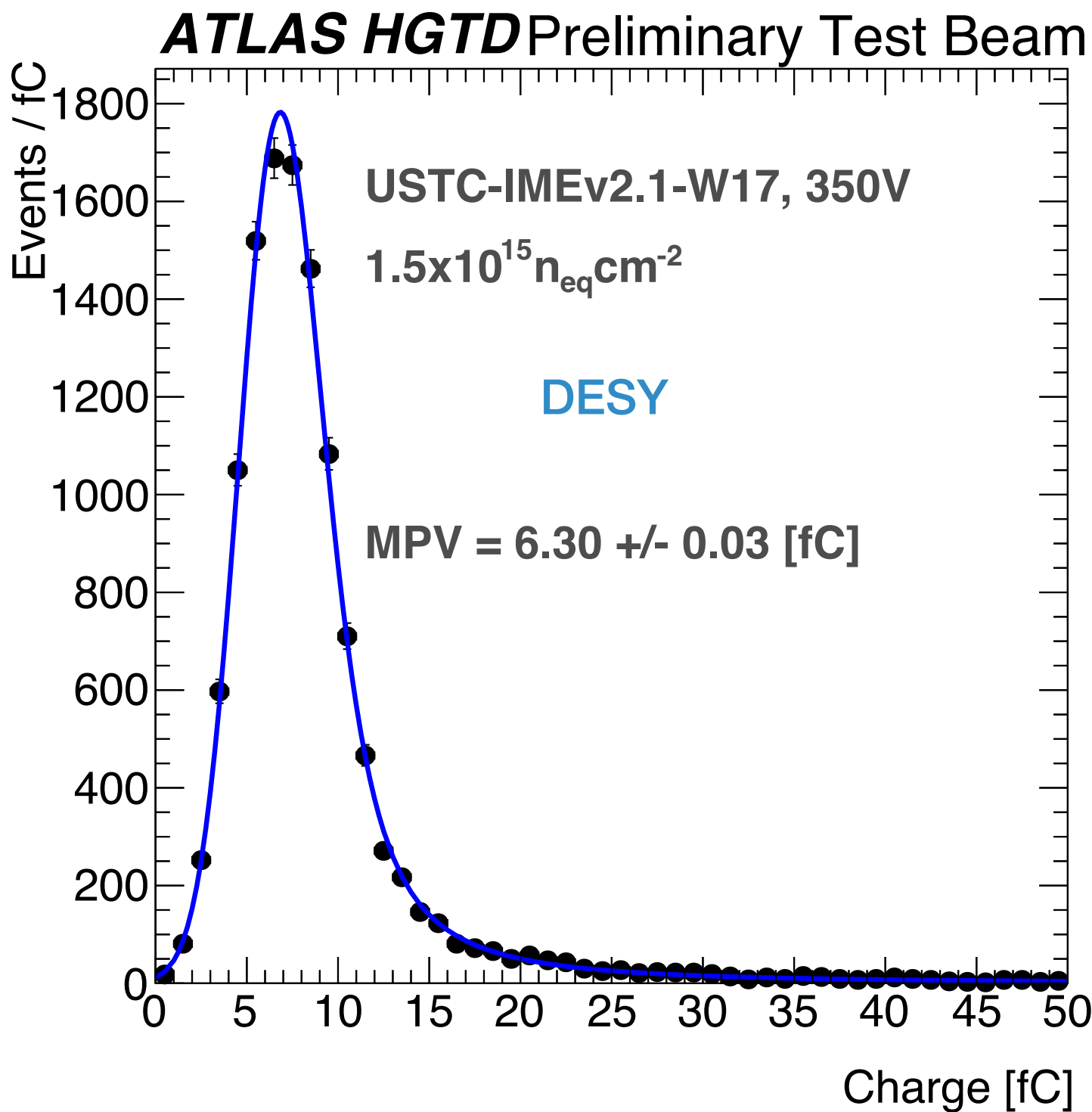
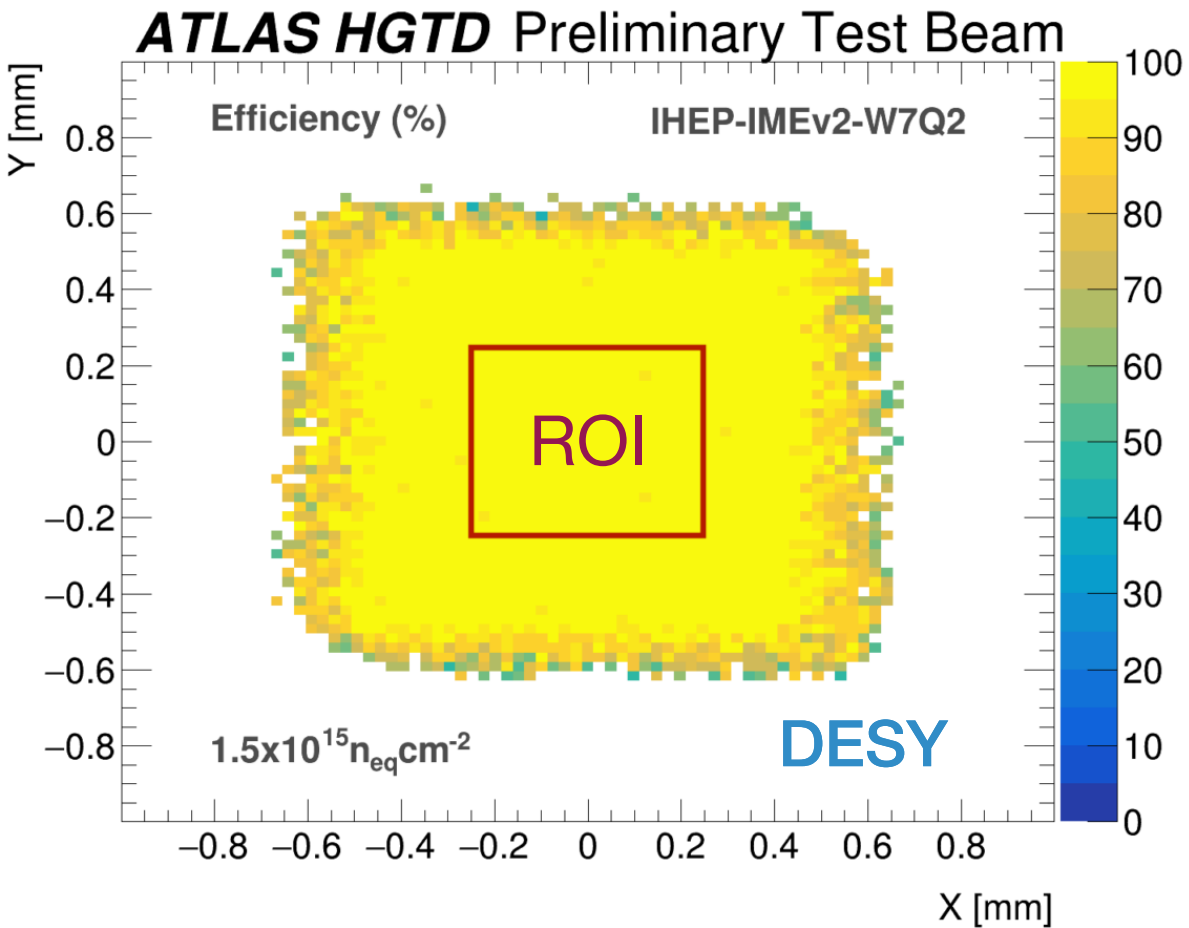




# Results: charge collection

## Charge

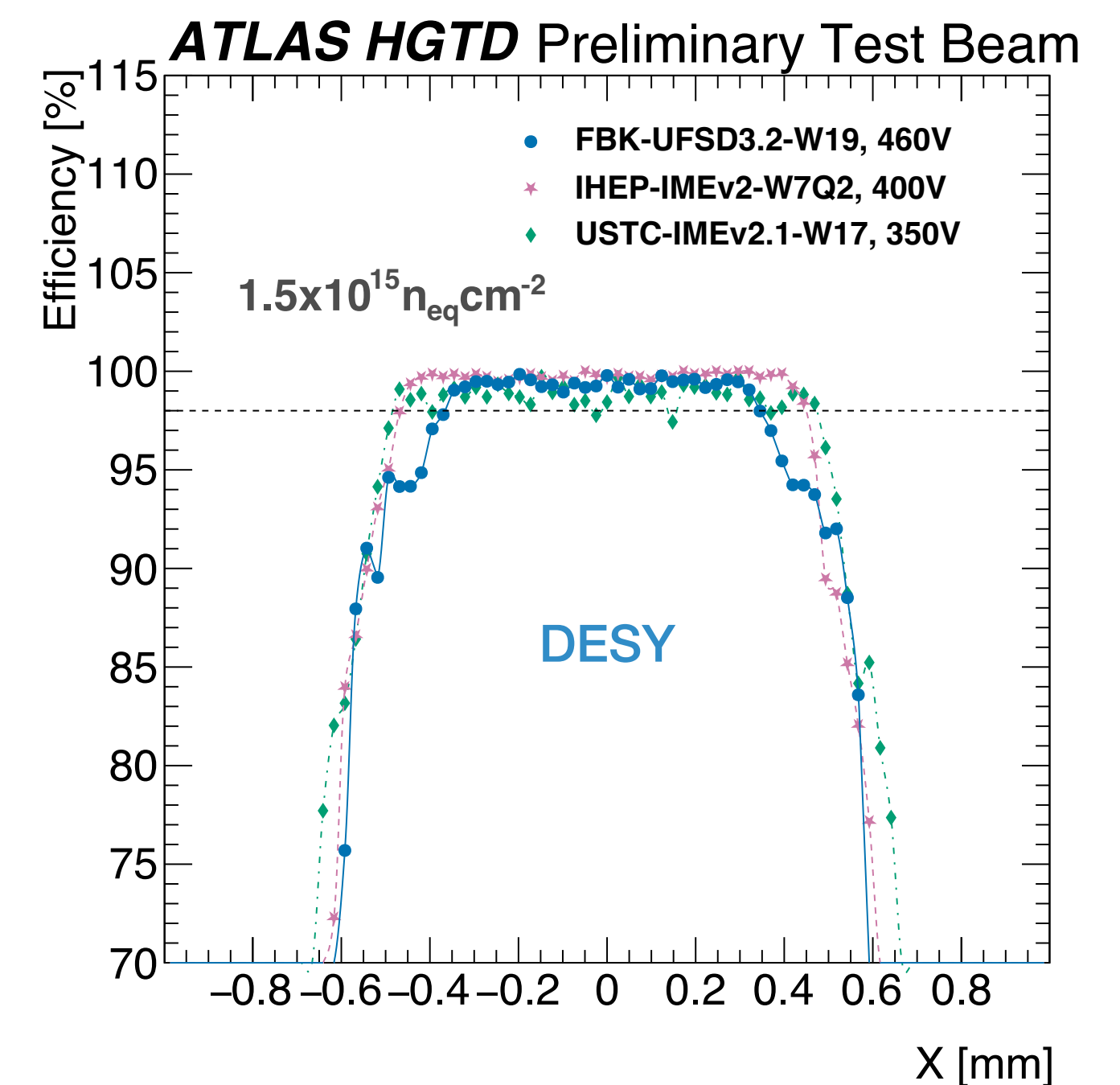
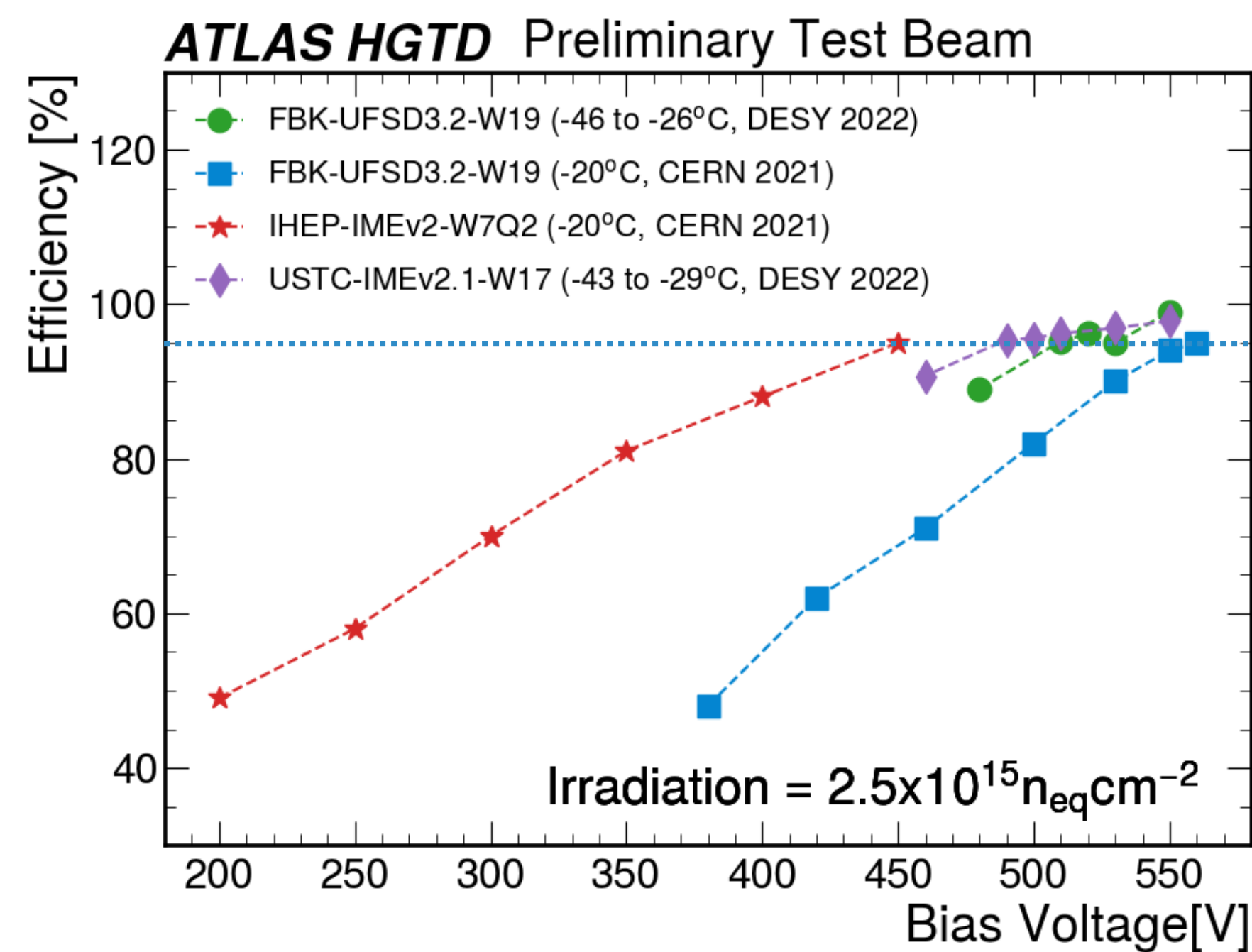
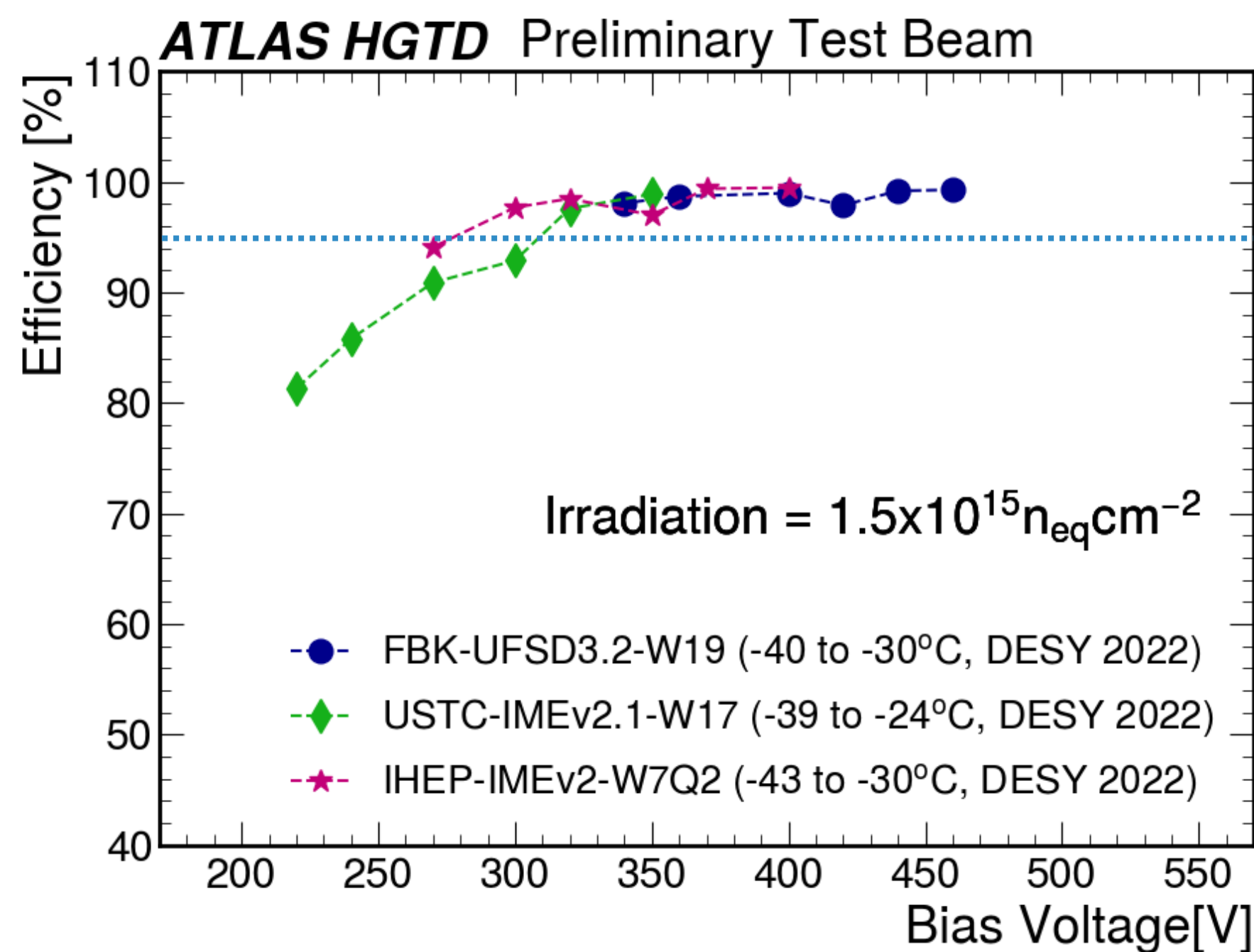
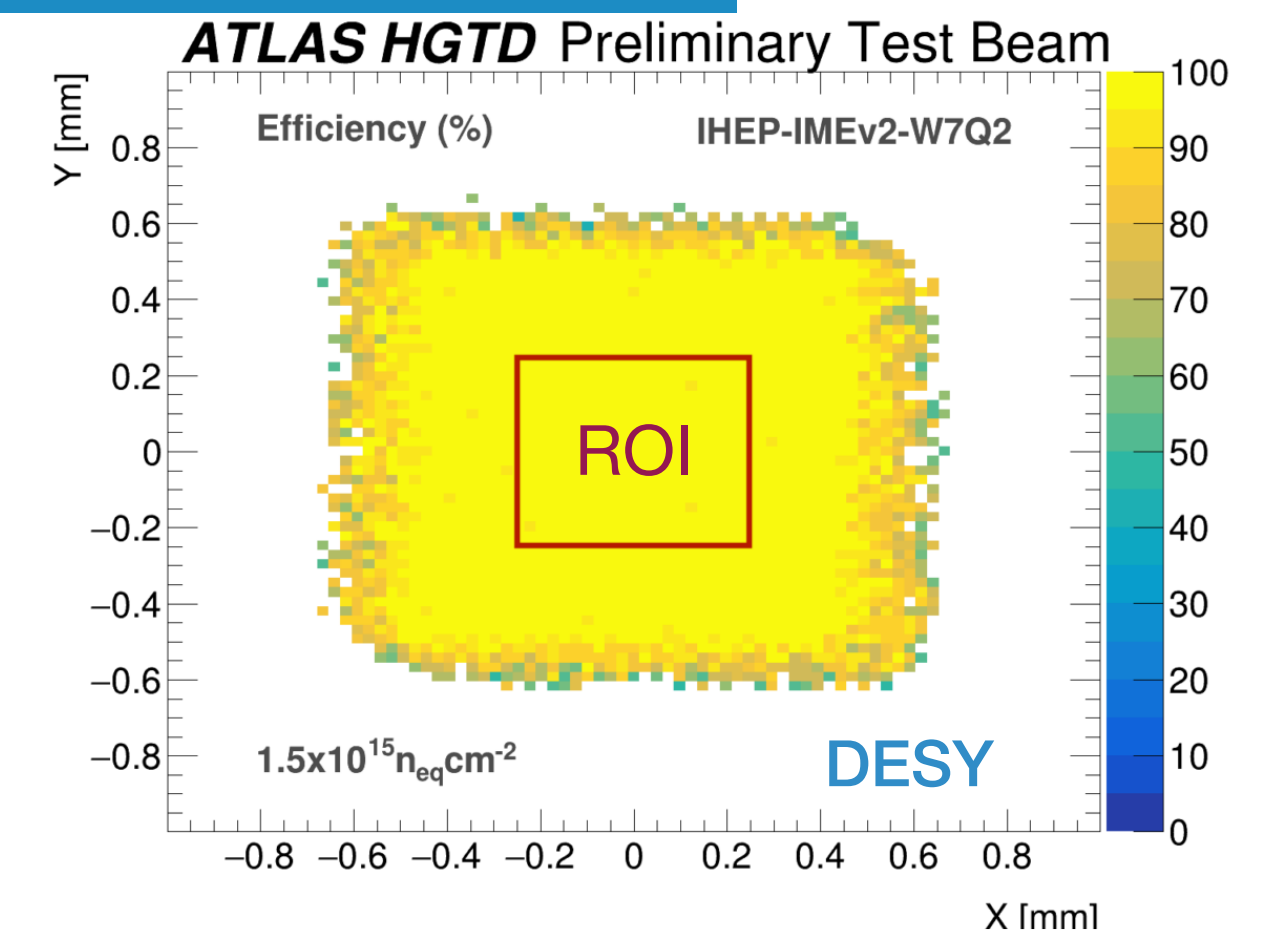
- Fit charge distribution in the ROI with convolution of Landau & Gaus
- Extract the MPV to get the Charge value





# Results: efficiency

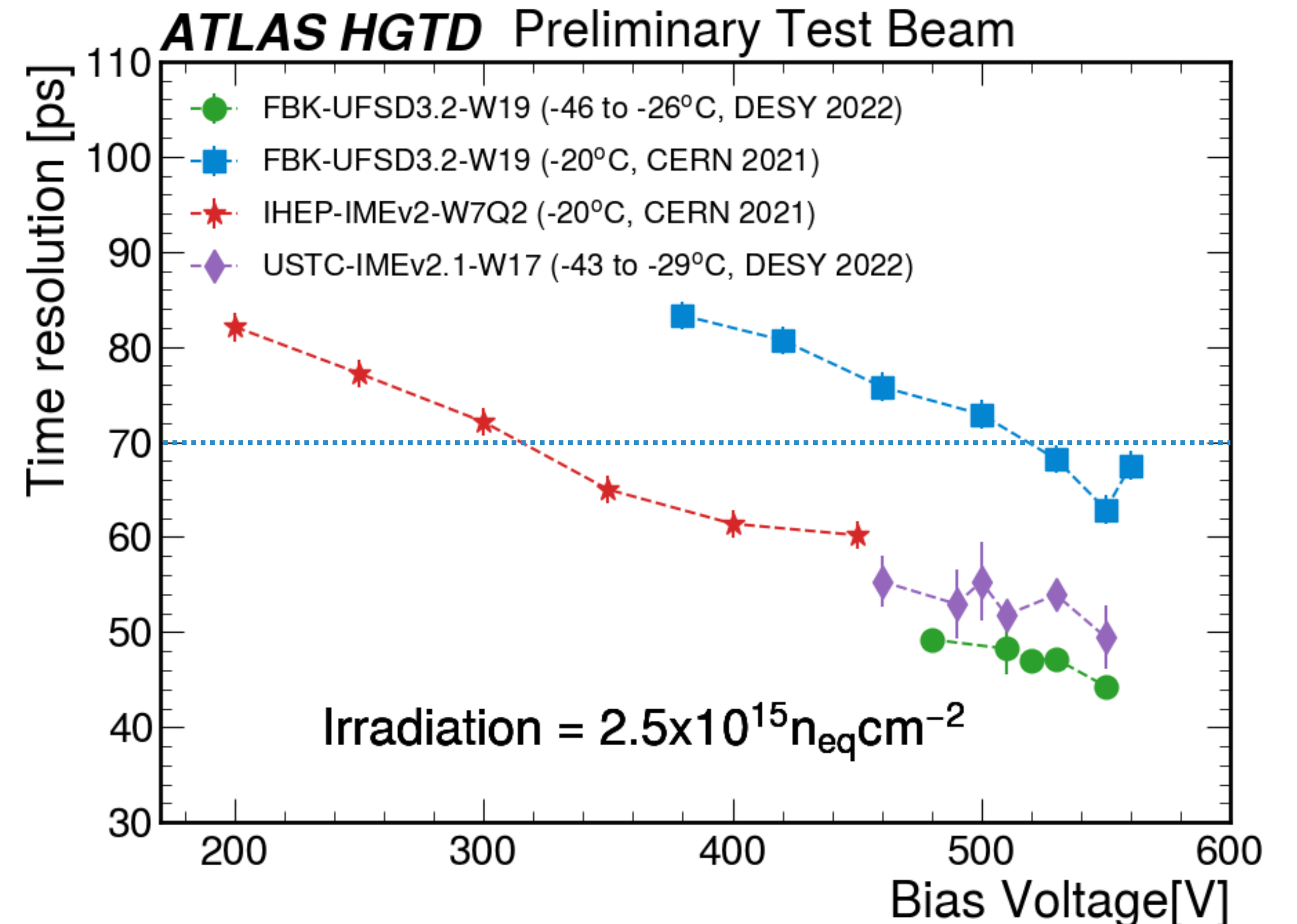
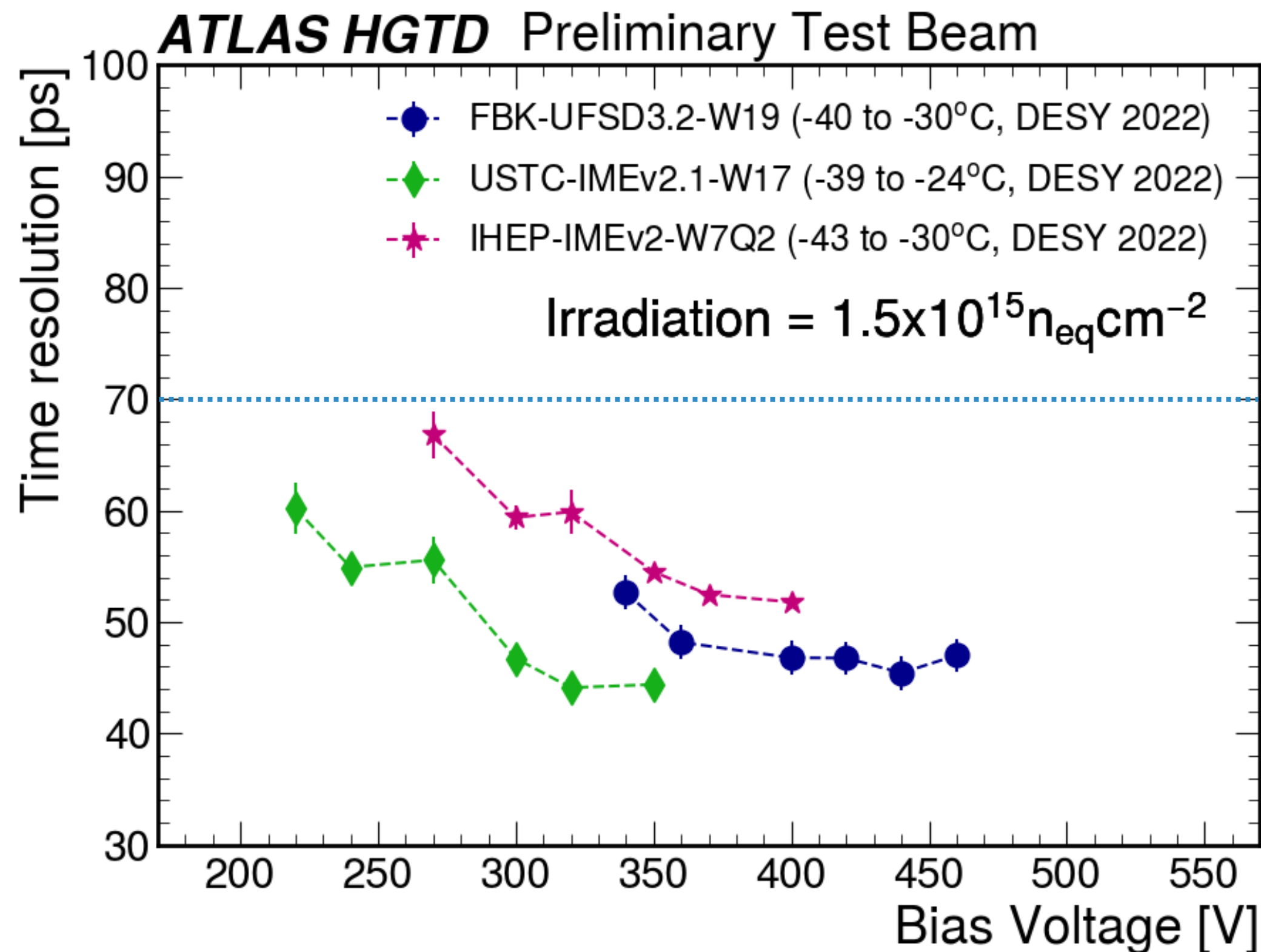
**Efficiency**  $\varepsilon = \frac{\text{\#hits in DUT passing the charge threshold (Q > 2fC)}}{\text{\#projected tracks in the DUT}}$



# Results: time resolution

Time resolution is computed from time difference distribution between the sensor and/or the SiPM or another sensor  $\sigma_{ij}$

Having 3 devices, the resolution of each one is calculated as 
$$\sigma_i = \sqrt{\frac{\sigma_{ij}^2 + \sigma_{ik}^2 - \sigma_{jk}^2}{2}}$$





Presented results have been essential to validate various sensor designs:

- Single Event Burnout resolved at voltages required to meet HGTD specifications
- Qualified performance of latest generation of Carbon diffused LGADs at the highest irradiation:
  - Efficiency of all presented sensors is  $> 98\%$  at  $1.5 \times 10^{15} n_{eq} / \text{cm}^2$  and is  $> 95\%$  at  $2.5 \times 10^{15} n_{eq} / \text{cm}^2$  going up to  $\sim 99\%$  for some sensors
  - Charge of all presented sensors is  $> 5 \text{ fC}$  at  $1.5 \times 10^{15} n_{eq} / \text{cm}^2$  and  $2.5 \times 10^{15} n_{eq} / \text{cm}^2$
  - Time resolution is lower than  $60 \text{ ps}$  for all the tested sensors at  $1.5 \times 10^{15} n_{eq} / \text{cm}^2$  and  $2.5 \times 10^{15} n_{eq} / \text{cm}^2$  and can get  $< 50 \text{ ps}$  for some sensors

Test Beam campaigns studying the combined performance of LGAD + ALTIROC have started this summer

**Thank you for your attention!**